Quad 2-Input Exclusive OR Gate

High-Performance Silicon-Gate CMOS

The MC74HC86A is identical in pinout to the LS86. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with JEDEC Standard No. 7 A Requirements
- Chip Complexity: 56 FETs or 14 Equivalent Gates
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant



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MARKING DIAGRAMS

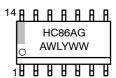


PDIP-14 N SUFFIX CASE 646





SOIC-14 D SUFFIX CASE 751A



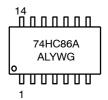


TSSOP-14 DT SUFFIX CASE 948G





SOEIAJ-14 F SUFFIX CASE 965



A = Assembly Location

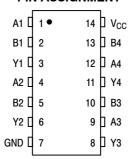
L, WL = Wafer Lot Y, YY = Year W, WW = Work Week G or = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

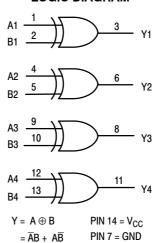
PIN ASSIGNMENT



FUNCTION TABLE

| Inp | Output | |
|-----|--------|---|
| Α | В | Υ |
| L | L | L |
| L | Н | Н |
| Н | L | Н |
| Н | Н | L |

LOGIC DIAGRAM



ORDERING INFORMATION

| Device | Package | Shipping [†] |
|----------------|------------------------|-----------------------|
| MC74HC86ANG | PDIP-14 (Pb-Free) | 25 Units / Rail |
| MC74HC86ADG | SOIC-14 (Pb-Free) | 55 Units / Rail |
| MC74HC86ADR2G | SOIC-14 (Pb-Free) | 2500 / Tape & Reel |
| MC74HC86ADTR2G | TSSOP-14* | 2500 / Tape & Reel |
| MC74HC86AFG | SOEIAJ-14 (Pb-Free) | 50 Units / Rail |
| MC74HC86AFELG | SOEIAJ-14 (Pb-Free) | 2000 / Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}This package is inherently Pb-Free.

MAXIMUM RATINGS

| Symbol | Parameter | | Value | Unit |
|------------------|---|---|-------------------|------|
| V _{CC} | DC Supply Voltage (Referenced | DC Supply Voltage (Referenced to GND) | | |
| V _{in} | DC Input Voltage (Referenced to | DC Input Voltage (Referenced to GND) | | |
| V _{out} | DC Output Voltage (Referenced | - 0.5 to V _{CC} + 0.5 | V | |
| l _{in} | DC Input Current, per Pin | ± 20 | mA | |
| l _{out} | DC Output Current, per Pin | ± 25 | mA | |
| Icc | DC Supply Current, V _{CC} and GN | D Pins | ± 50 | mA |
| P_{D} | Power Dissipation in Still Air, | Plastic DIP† SOIC Package† TSSOP Package† | 750 500 450 | mW |
| T _{stg} | Storage Temperature | - 65 to + 150 | °C | |
| TL | Lead Temperature, 1 mm from C (Plastic DIP, SOIC | ase for 10 Seconds or TSSOP Package) | 260 | °C |

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C TSSOP Package: - 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | | | Max | Unit |
|------------------------------------|--|--|-------------|--------------------|------|
| V _{CC} | DC Supply Voltage (Referenced to GND) | | | 6.0 | V |
| V _{in} , V _{out} | DC Input Voltage, Output Voltage (Referen GND) | DC Input Voltage, Output Voltage (Referenced to GND) | | | V |
| T _A | Operating Temperature, All Package Types | ; | – 55 | + 125 | °C |
| t _r , t _f | (Figure 1) V | CC = 2.0 V CC = 4.5 V CC = 6.0 V | 000 | 1000 500 400 | ns |

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

| | | | | Gu | aranteed Li | mit | |
|-----------------|--------------------------------------|--|--------------------------|---------------------------|---------------------------|---------------------------|------|
| Symbol | Parameter | Test Conditions | V _{CC} V | – 55 to 25°C | ≤ 85 °C | ≤ 125°C | Unit |
| V _{IH} | Minimum High-Level Input Voltage | $V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$ | 2.0 3.0 4.5 6.0 | 1.5 2.1 3.15 4.2 | 1.5 2.1 3.15 4.2 | 1.5 2.1 3.15 4.2 | V |
| V _{IL} | Maximum Low-Level Input Voltage | $V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$ | 2.0 3.0 4.5 6.0 | 0.5 0.9 1.35 1.8 | 0.5 0.9 1.35 1.8 | 0.5 0.9 1.35 1.8 | V |
| V _{OH} | Minimum High-Level Output Voltage | $V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$ | 2.0 4.5 6.0 | 1.9 4.4 5.9 | 1.9 4.4 5.9 | 1.9 4.4 5.9 | V |
| | | $ \begin{vmatrix} V_{in} = V_{IH} \text{ or } V_{IL} & I_{out} \leq 2.4 \text{ mA} \\ I_{out} \leq 4.0 \text{ mA} \\ I_{out} \leq 5.2 \text{ mA} \end{vmatrix} $ | 3.0 4.5 6.0 | 2.48 3.98 5.48 | 2.34 3.84 5.34 | 2.20 3.70 5.20 | |
| V _{OL} | Maximum Low-Level Output Voltage | $ V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$ | 2.0 4.5 6.0 | 0.1 0.1 0.1 | 0.1 0.1 0.1 | 0.1 0.1 0.1 | V |
| | | $ \begin{aligned} V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} & & I_{\text{out}} \leq 2.4 \text{ mA} \\ & I_{\text{out}} \leq 4.0 \text{ mA} \\ & I_{\text{out}} \leq 5.2 \text{ mA} \end{aligned} $ | 3.0 4.5 6.0 | 0.26 0.26 0.26 | 0.33 0.33 0.33 | 0.40 0.40 0.40 | |

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

| | | | | Gu | aranteed Li | mit | |
|-----------------|--|---|-----------------|-----------------|----------------|---------|------|
| Symbol | Parameter | Test Conditions | V _{CC} | – 55 to 25°C | ≤ 85 °C | ≤ 125°C | Unit |
| l _{in} | Maximum Input Leakage Current | V _{in} = V _{CC} or GND | 6.0 | ± 0.1 | ± 1.0 | ± 1.0 | μΑ |
| I _{CC} | Maximum Quiescent Supply Current (per Package) | $V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$ | 6.0 | 1.0 | 10 | 40 | μΑ |

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t, = t_f = 6 ns)

| | | | Gu | aranteed Li | mit | |
|---|---|--------------------------|-----------------------|------------------------|------------------------|------|
| Symbol | Parameter | V _{CC} V | – 55 to 25°C | ≤ 85 °C | ≤ 125°C | Unit |
| t _{PLH} , t _{PHL} | Maximum Propagation Delay, Input A or B to Output Y (Figures 1 and 2) | 2.0 3.0 4.5 6.0 | 100 80 20 17 | 125 90 25 21 | 150 110 31 26 | ns |
| t _{TLH} , t _{THL} | Maximum Output Transition Time, Any Output (Figures 1 and 2) | 2.0 3.0 4.5 6.0 | 75 30 15 13 | 95 40 19 16 | 110 55 22 19 | ns |
| C _{in} | Maximum Input Capacitance | _ | 10 | 10 | 10 | pF |
| | | | Typical | @ 25°C, V _C | _C = 5.0 V | |
| C _{PD} Power Dissipation Capacitance (Per Gate)* | | | 33 | | pF | |

C_{PD} Power Dissipation Capacitance (Per Gate)*

^{*}Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

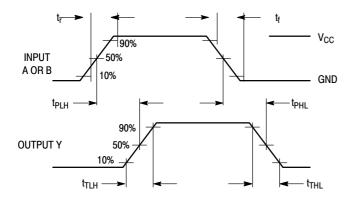
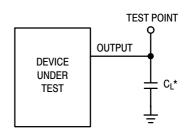


Figure 1. Switching Waveforms



*Includes all probe and jig capacitance

Figure 2. Test Circuit

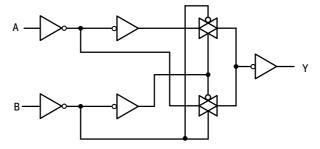
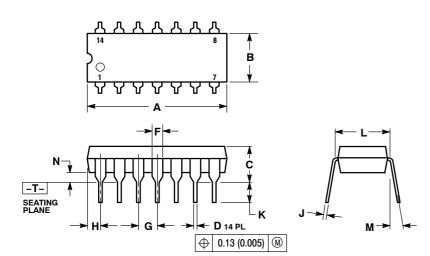


Figure 3. Expanded Logic Diagram (1/4 of Device)

PACKAGE DIMENSIONS

PDIP-14 **N SUFFIX** CASE 646-06 ISSUE P

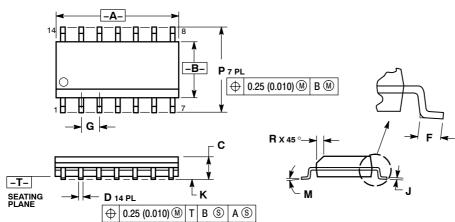


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
 5. ROUNDED CORNERS OPTIONAL.

| | INCHES | | MILLIM | IETERS |
|-----|--------|-------|--------|--------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.715 | 0.770 | 18.16 | 19.56 |
| В | 0.240 | 0.260 | 6.10 | 6.60 |
| С | 0.145 | 0.185 | 3.69 | 4.69 |
| D | 0.015 | 0.021 | 0.38 | 0.53 |
| F | 0.040 | 0.070 | 1.02 | 1.78 |
| G | 0.100 | BSC | 2.54 | BSC |
| Н | 0.052 | 0.095 | 1.32 | 2.41 |
| J | 0.008 | 0.015 | 0.20 | 0.38 |
| K | 0.115 | 0.135 | 2.92 | 3.43 |
| L | 0.290 | 0.310 | 7.37 | 7.87 |
| М | | 10 ° | | 10 ° |
| N | 0.015 | 0.039 | 0.38 | 1.01 |

PACKAGE DIMENSIONS

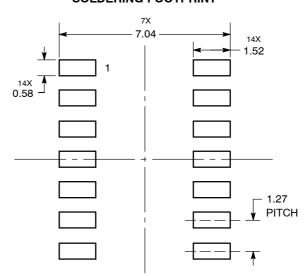
SOIC-14 **D SUFFIX** CASE 751A-03 **ISSUE J**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

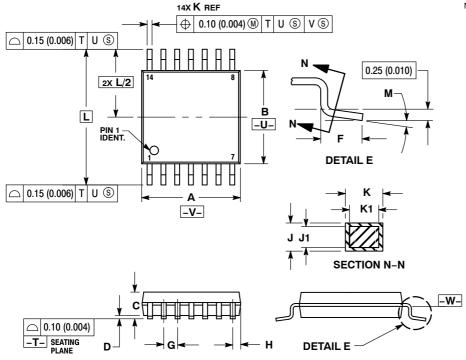
| | MILLIMETERS | | INC | HES |
|-----|-------------|------|-----------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 8.55 | 8.75 | 0.337 | 0.344 |
| В | 3.80 | 4.00 | 0.150 | 0.157 |
| С | 1.35 | 1.75 | 0.054 | 0.068 |
| D | 0.35 | 0.49 | 0.014 | 0.019 |
| F | 0.40 | 1.25 | 0.016 | 0.049 |
| G | 1.27 | BSC | 0.050 BSC | |
| J | 0.19 | 0.25 | 0.008 | 0.009 |
| K | 0.10 | 0.25 | 0.004 | 0.009 |
| М | 0 ° | 7 ° | 0 ° | 7° |
| Р | 5.80 | 6.20 | 0.228 | 0.244 |
| R | 0.25 | 0.50 | 0.010 | 0.019 |

SOLDERING FOOTPRINT



PACKAGE DIMENSIONS

TSSOP-14 **DT SUFFIX** CASE 948G-01 ISSUE B



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

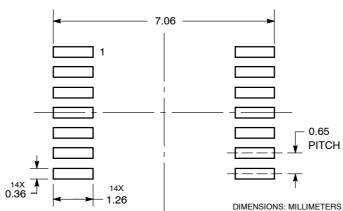
 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 - DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
 - INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
 NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE
 DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.08
 (0.003) TOTAL IN EXCESS OF THE K
 DIMENSION AT MAXIMUM MATERIAL
 CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN FOR
 REFERENCE ONLY

 - REFERENCE ONLY.
 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

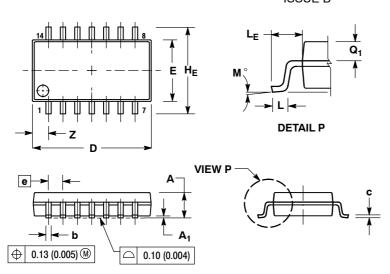
| | MILLIN | IETERS | INC | HES |
|-----|--------|--------|-----------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 4.90 | 5.10 | 0.193 | 0.200 |
| В | 4.30 | 4.50 | 0.169 | 0.177 |
| С | | 1.20 | | 0.047 |
| D | 0.05 | 0.15 | 0.002 | 0.006 |
| F | 0.50 | 0.75 | 0.020 | 0.030 |
| G | 0.65 | BSC | 0.026 BSC | |
| Н | 0.50 | 0.60 | 0.020 | 0.024 |
| J | 0.09 | 0.20 | 0.004 | 0.008 |
| J1 | 0.09 | 0.16 | 0.004 | 0.006 |
| Κ | 0.19 | 0.30 | 0.007 | 0.012 |
| K1 | 0.19 | 0.25 | 0.007 | 0.010 |
| L | 6.40 | BSC | 0.252 BSC | |
| М | 0 ° | 8 ° | 0 ° | 8 ° |

SOLDERING FOOTPRINT



PACKAGE DIMENSIONS

SOEIAJ-14 **F SUFFIX** CASE 965-01 **ISSUE B**



NOTES:

- 1. DIMENO... Y14.5M, 1982. DIMENSIONING AND TOLERANCING PER ANSI
- CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS D AND E DO NOT INCLUDE
- MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE, MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY. 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH
 DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER
 RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

| | MILLIMETERS | | ILLIMETERS INCHES | |
|----------------|-------------|-------|-------------------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | | 2.05 | | 0.081 |
| A ₁ | 0.05 | 0.20 | 0.002 | 0.008 |
| b | 0.35 | 0.50 | 0.014 | 0.020 |
| С | 0.10 | 0.20 | 0.004 | 0.008 |
| D | 9.90 | 10.50 | 0.390 | 0.413 |
| Е | 5.10 | 5.45 | 0.201 | 0.215 |
| е | 1.27 | BSC | 0.050 BSC | |
| HE | 7.40 | 8.20 | 0.291 | 0.323 |
| ٦ | 0.50 | 0.85 | 0.020 | 0.033 |
| LE | 1.10 | 1.50 | 0.043 | 0.059 |
| М | 0 ° | 10° | 0 ° | 10° |
| Q_1 | 0.70 | 0.90 | 0.028 | 0.035 |
| Z | | 1.42 | | 0.056 |

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